

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (previously presented): A method for generating radicals comprising:
feeding F₂ gas or a mixed gas of F₂ gas and an inert gas into a chamber of which the inside is provided with a carbon material,
supplying a carbon atom from the carbon material by applying a target bias voltage to the carbon material, and
thereby generating radicals,
wherein the bias voltage of 480 to 600 V is applied to the carbon material to selectively form CF₃ radical and thereby CF₃ radical is generated.
2. (original): The method for generating radicals according to claim 1, wherein the carbon atom is generated by magnetron sputtering of the carbon material.
3. (previously presented): The method for generating radicals according to claim 1, wherein the target bias voltage is applied to the carbon material by a dual frequency combined magnetron in which a high frequency power source and a low frequency power source are connected in parallel.
- 4 - 7. (canceled).

8. (previously presented): A method for etching a silicon oxide film comprising:
etching a silicon oxide film using CF_3 radical generated by the method for generating radicals
according to claim 1.

9 - 12 (canceled).